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FQP45N15V2 / FQPF45N15V2

N-Channel QFET® MOSFET

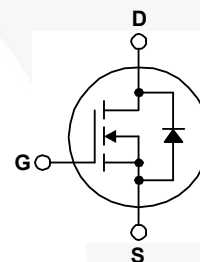
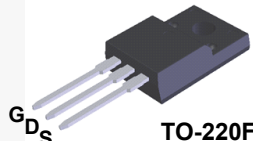
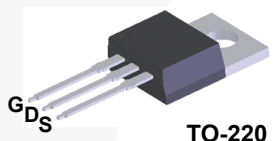
150 V, 45 A, 40 mΩ

Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- 45 A, 150 V, $R_{DS(on)} = 40 \text{ m}\Omega$ (Max.) @ $V_{GS} = 10 \text{ V}$, $I_D = 22.5 \text{ A}$
- Low Gate Charge (Typ. 72 nC)
- Low C_{rss} (Typ. 135 pF)
- 100% Avalanche Tested



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FQP45N15V2	FQPF45N15V2	Unit
V_{DSS}	Drain-Source Voltage	150		V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$) - Continuous ($T_C = 100^\circ\text{C}$)	45	45 *	A
		31	31 *	A
I_{DM}	Drain Current - Pulsed (Note 1)	180	180 *	A
V_{GSS}	Gate-Source Voltage	± 30		V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	1124		mJ
I_{AR}	Avalanche Current (Note 1)	45		A
E_{AR}	Repetitive Avalanche Energy (Note 1)	22		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5		V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$) - Derate above 25°C	220	66	W
		1.47	0.44	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150		$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300		$^\circ\text{C}$

* Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	FQP45N15V2	FQPF45N15V2	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.68	2.25	$^\circ\text{C}/\text{W}$
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.5	--	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	62.5	$^\circ\text{C}/\text{W}$

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP45N15V2	PV245N15	TO-220	Tube	N/A	N/A	50 units
FQPF45N15V2	FQPF45N15V2	TO-220F	Tube	N/A	N/A	50 units

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	150	--	--	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C	--	0.21	--	V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 150\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
		$V_{DS} = 120\text{ V}, T_C = 150^\circ\text{C}$	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 22.5\text{ A}$	--	0.034	0.04	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 22.5\text{ A}$	--	40	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	2330	3030	pF
C_{oss}	Output Capacitance		--	510	670	pF
C_{rfs}	Reverse Transfer Capacitance		--	135	176	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 75\text{ V}, I_D = 45\text{ A},$ $R_G = 25\ \Omega$	--	22	54	ns
t_r	Turn-On Rise Time		--	232	474	ns
$t_{d(off)}$	Turn-Off Delay Time		--	224	458	ns
t_f	Turn-Off Fall Time		(Note 4)	--	246	502
Q_g	Total Gate Charge	$V_{DS} = 120\text{ V}, I_D = 45\text{ A},$ $V_{GS} = 10\text{ V}$	--	72	94	nC
Q_{gs}	Gate-Source Charge		--	13	--	nC
Q_{gd}	Gate-Drain Charge		(Note 4)	--	31	--

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current	--	--	45	A	
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	180	A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 45\text{ A}$	--	--	1.4	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 45\text{ A},$ $di_F / dt = 100\text{ A}/\mu\text{s}$	--	176	--	ns
Q_{rr}	Reverse Recovery Charge		--	1.19	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 0.74\text{ mH}, I_{AS} = 45\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 45\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Essentially independent of operating temperature

Typical Characteristics

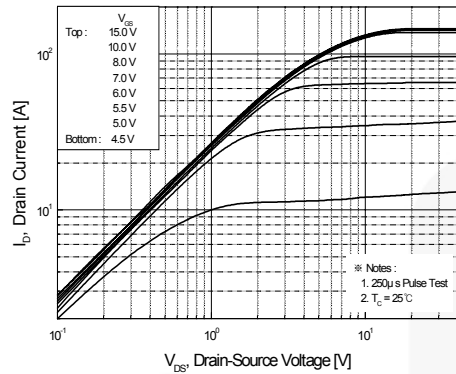


Figure 1. On-Region Characteristics

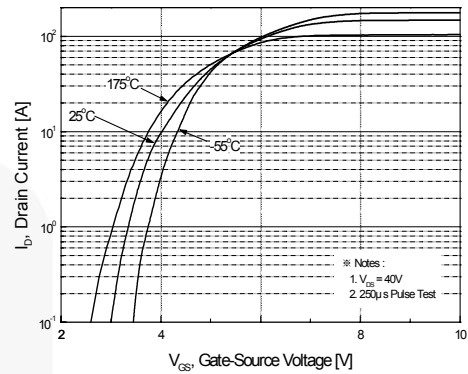


Figure 2. Transfer Characteristics

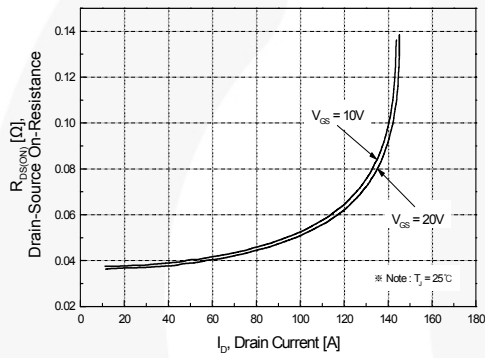


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

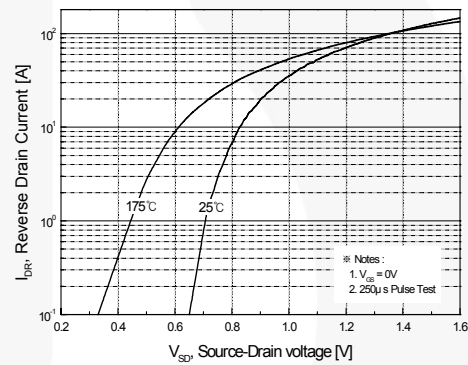


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

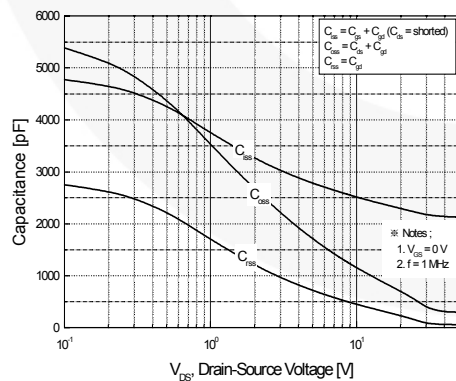


Figure 5. Capacitance Characteristics

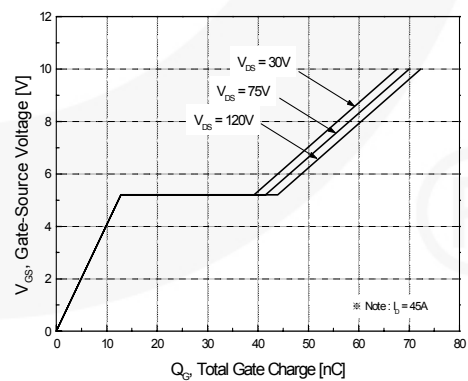


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

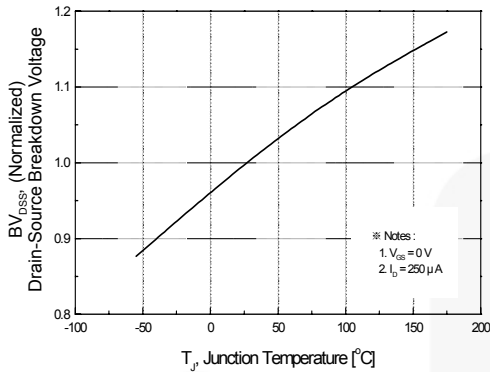


Figure 7. Breakdown Voltage Variation vs Temperature

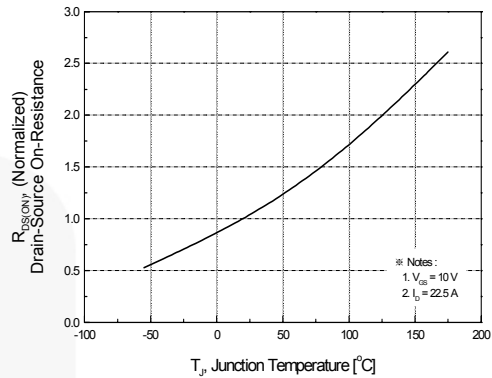


Figure 8. On-Resistance Variation vs Temperature

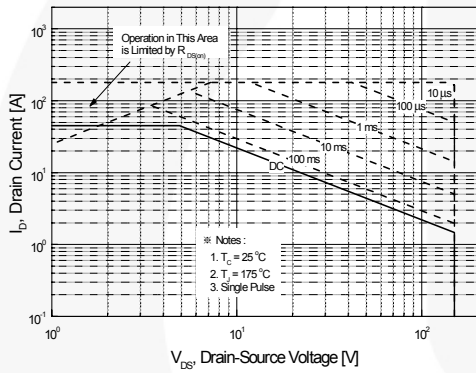


Figure 9-1. Maximum Safe Operating Area for FQP45N15V2

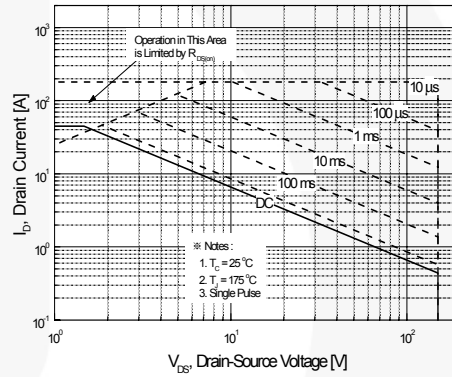


Figure 9-2. Maximum Safe Operating Area for FQPF45N15V2

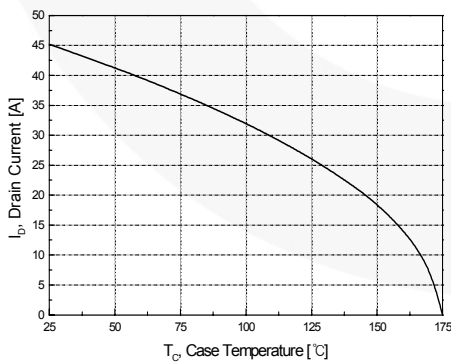


Figure 10. Maximum Drain Current vs Case Temperature

Typical Characteristics (Continued)

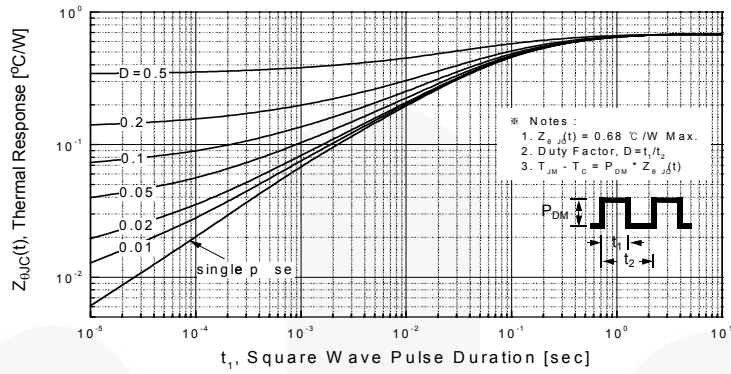


Figure 11. Transient Thermal Response Curve for FQP45N15V2

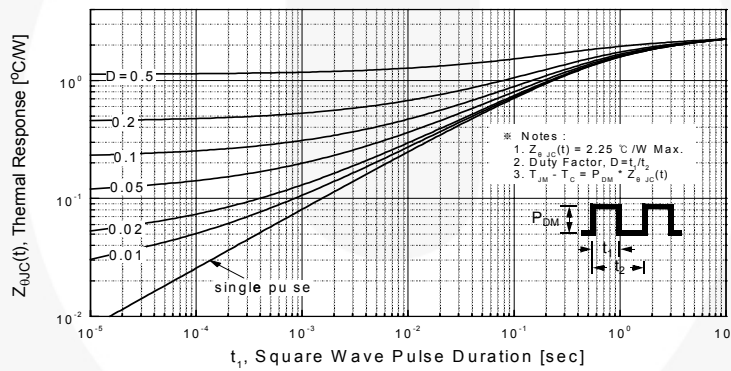


Figure 11-2. Transient Thermal Response Curve for FQPF45N15V2

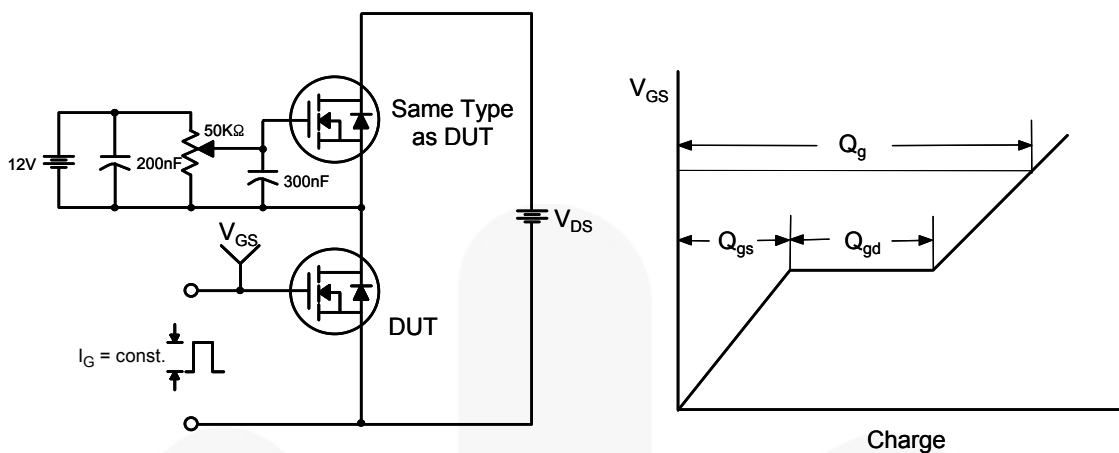


Figure 12. Gate Charge Test Circuit & Waveform

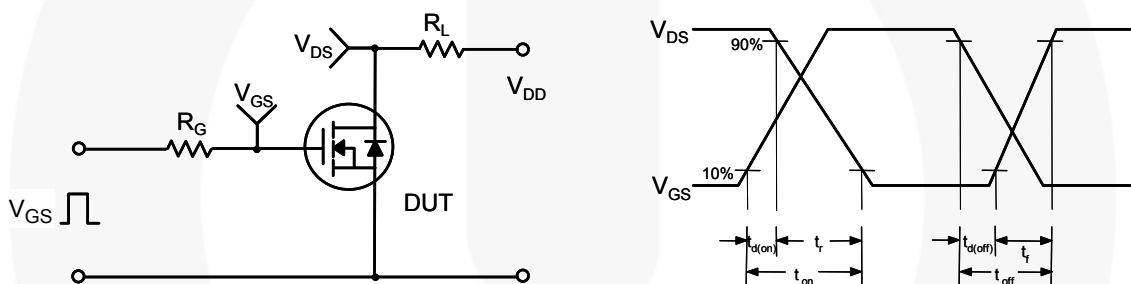


Figure 13. Resistive Switching Test Circuit & Waveforms

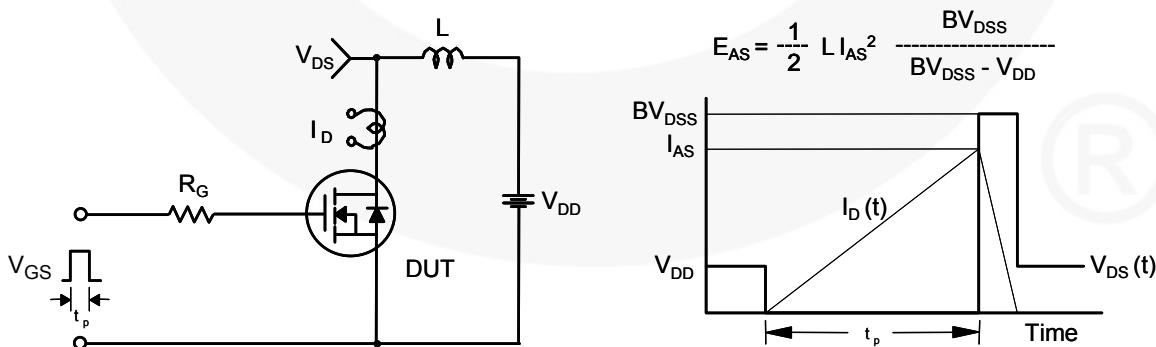


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

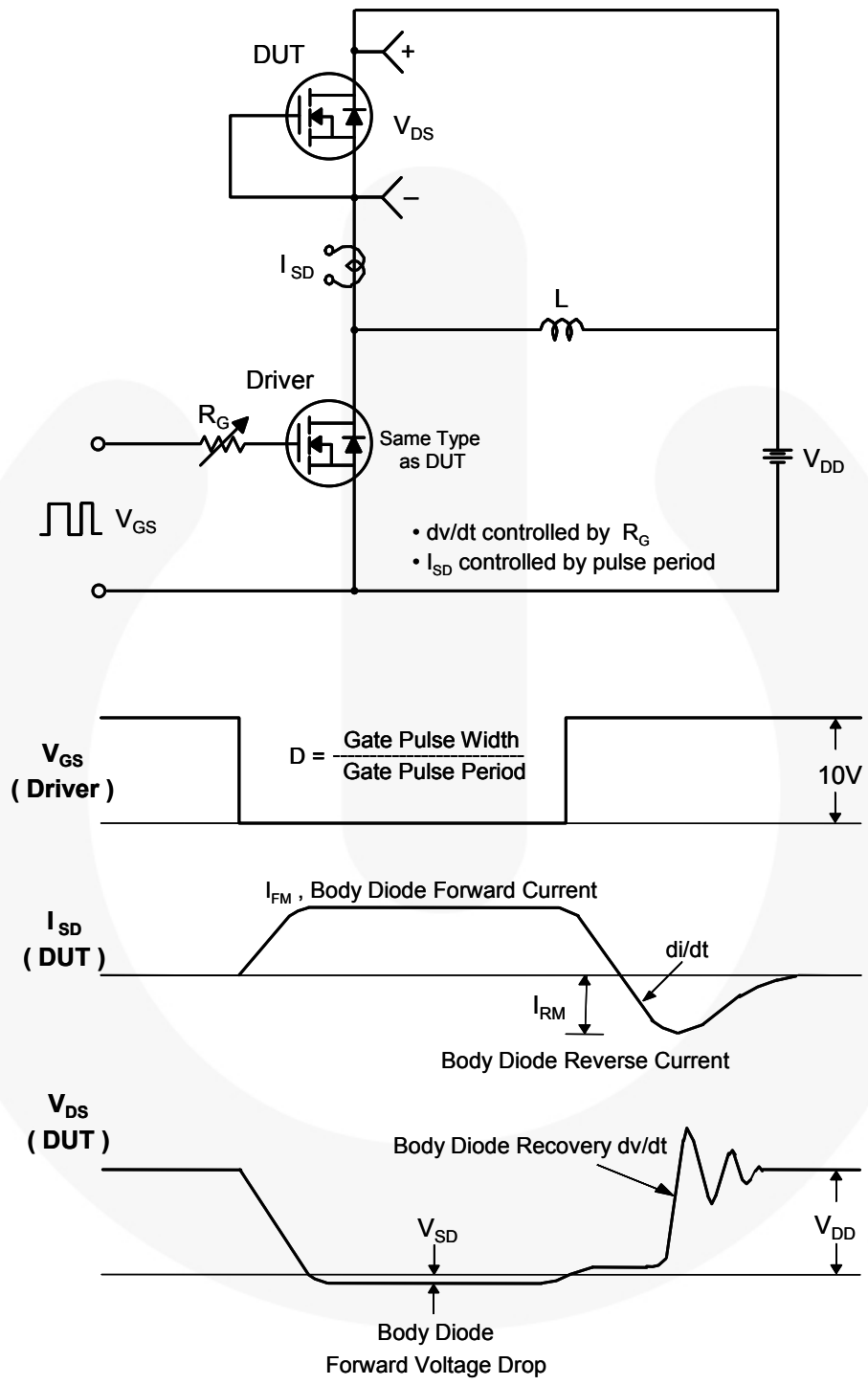


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

TO-220 3L

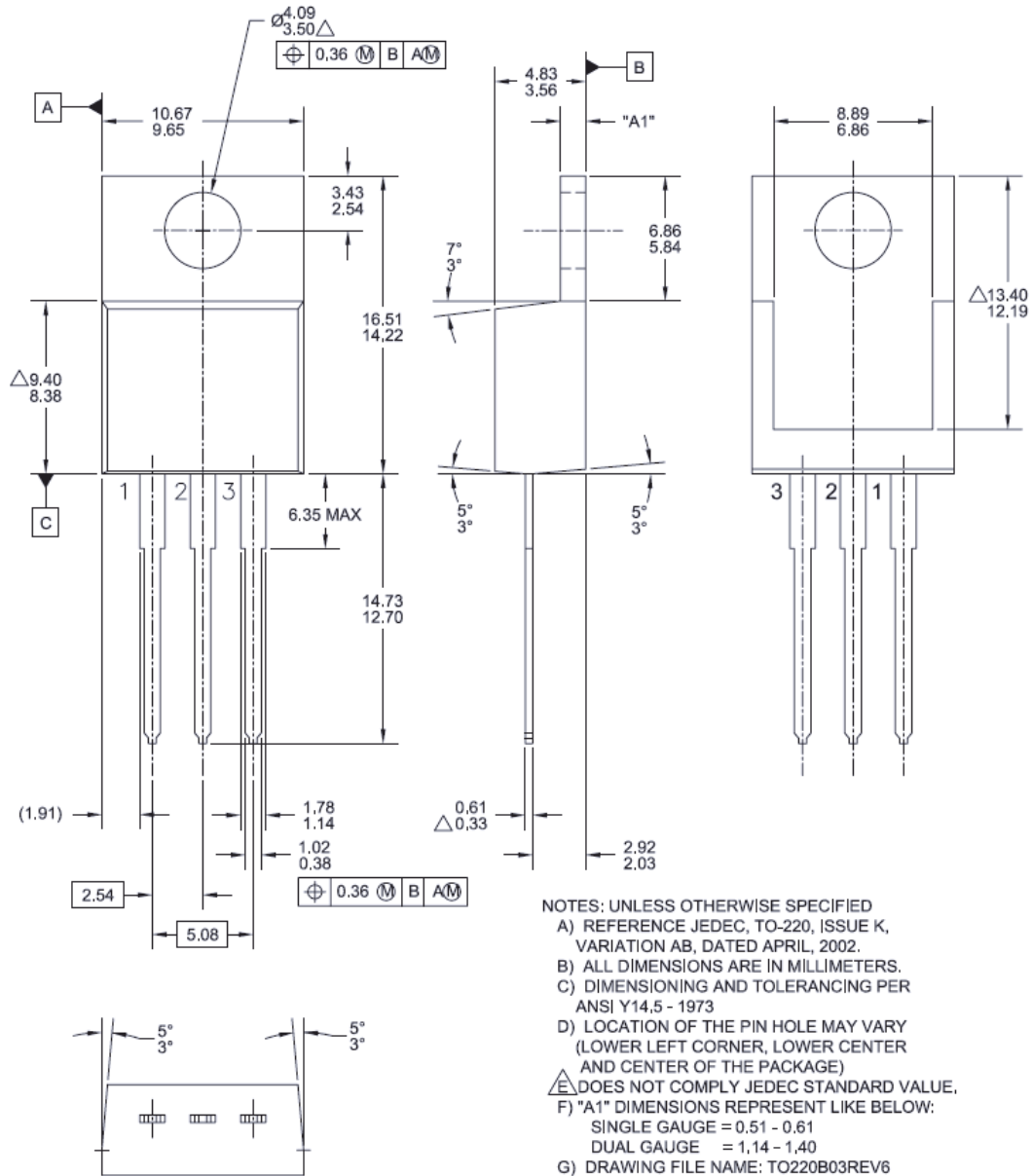


Figure 16. TO-220, Molded, 3Lead, Jeduc Variation AB

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Dimension in Millimeters

Mechanical Dimensions

TO-220F 3L

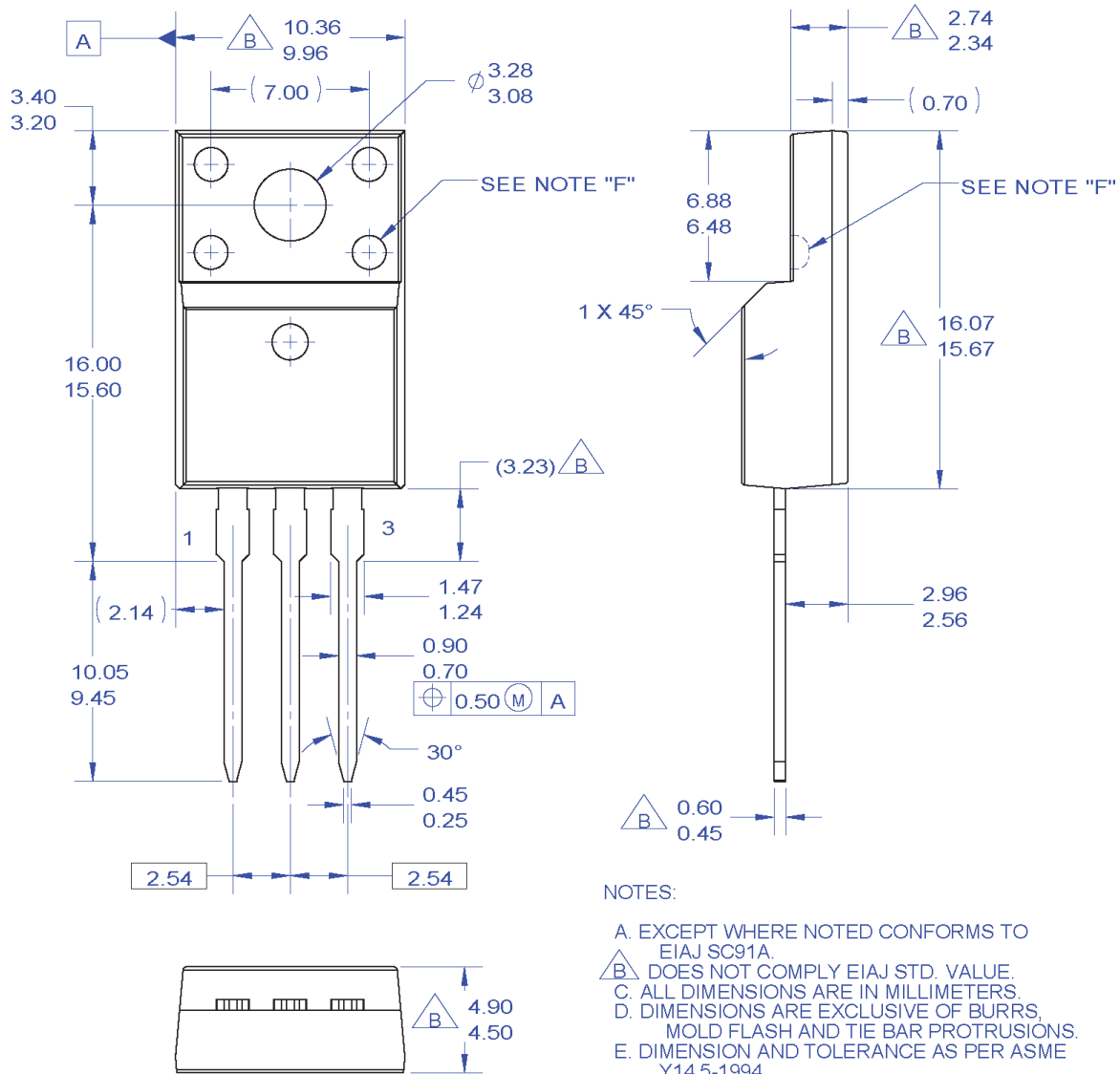


Figure 17. TO220, Molded, 3LD, Full Pack, EIAJ SC91, Straight Lead

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Dimension in Millimeters



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Rev. I66